

Charge transport in perovskites solar cells: modeling, analysis and simulations



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NUMSEMIC

Numerical Methods for
Innovative Semiconductor Devices

joint work with

Dilara Abdel (WIAS), Claire Chainais-Hillairet (Inria Lille), Maxime Herda (Inria Lille)

Inria-ECDF Partnership Kick-Off Workshop

6 June 2024

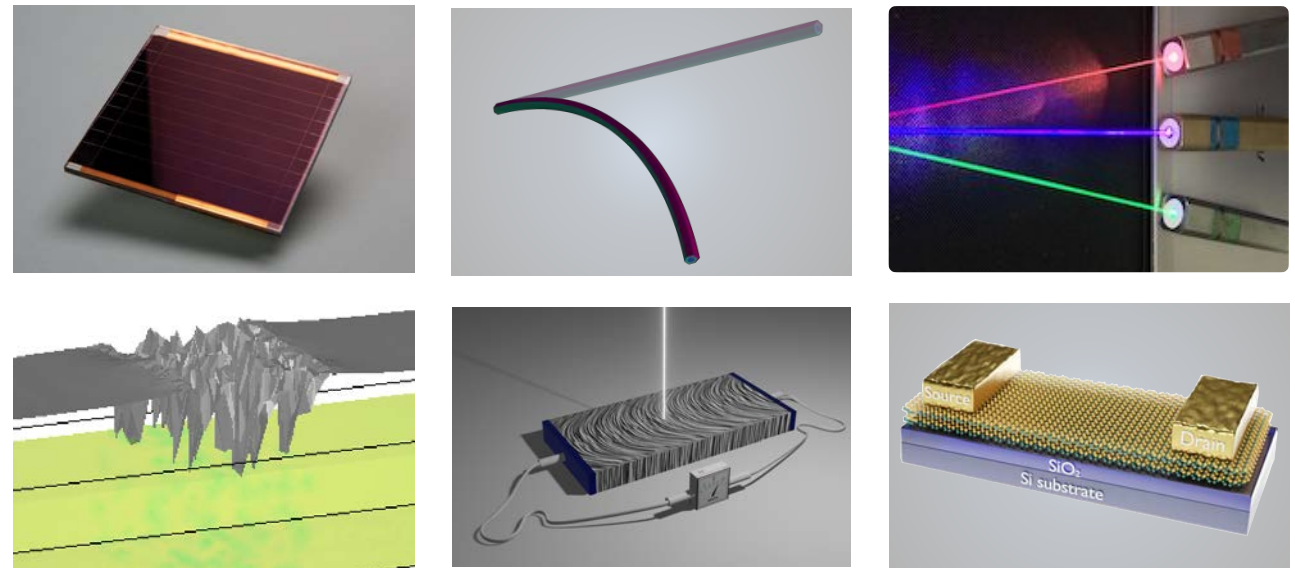


@numsemic

Numerical Methods for Innovative Semiconductor Devices

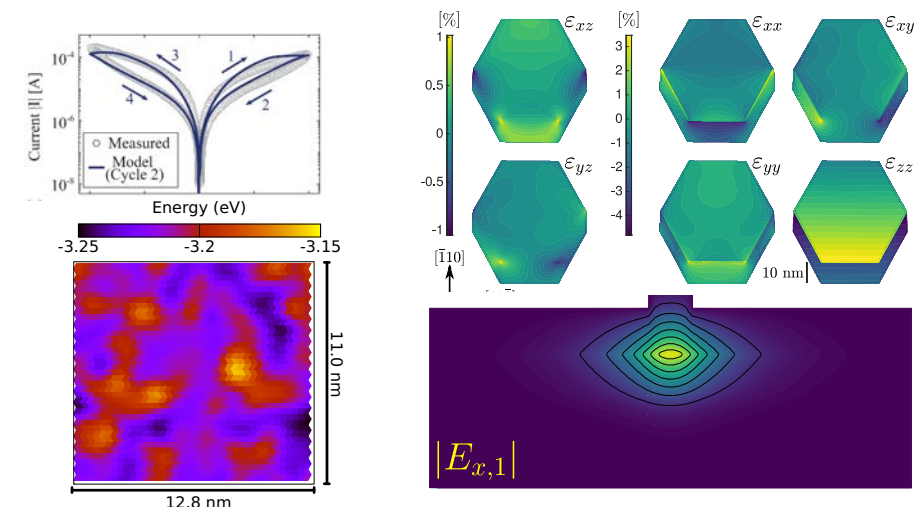
Applications

- ▶ perovskites
- ▶ quantum wells
- ▶ lasers
- ▶ bending nanowires
- ▶ crystal quality
- ▶ 2D TMDC memristors



Mathematical topics

- ▶ charge transport (“van Roosbroeck system”)
- ▶ finite strain elasticity models
- ▶ Helmholtz equation
- ▶ meshfree, multiscale, data-driven methods
- ▶ hysteresis, inverse problems, LLT



Collaborations

- ▶ 15 partners from mathematics, physics and engineering
Inria/U Lille, Oxford, U Florence, U Catania, TU Vienna, U Florence, U Pisa,
TU Ilmenau, U Rosario, Tyndall Institute, PDI, IHP, ZIB, HZB, IKZ

Existing collaboration



Patricio Farrell



Dilara Abdel



Claire Chainais-Hillairet



Maxime Herda

Existing collaboration



Patricio Farrell



Dilara Abdel



Jürgen Fuhrmann



Claire Chainais-Hillairet



Maxime Herda



Marianne Bessemoulin-Chatard (now Nantes)



Benoît Gaudeul (now U Paris Saclay)



Julien Moatti (now TU Vienna)

Existing collaboration



Patricio Farrell



Dilara Abdel



Jürgen Fuhrmann



Claire Chainais-Hillairet



Maxime Herda



Marianne Bessemoulin-
Chatard (now Nantes)



Benoît Gaudeul
(now U Paris Saclay)



Julien Moatti
(now TU Vienna)

- ▶ fruitful collaborations: theory driven by applications
- ▶ first joint publication by Chainais-Hillairet & Fuhrmann in 2012
- ▶ several research visits both ways

Solar cells based on...

Silicon

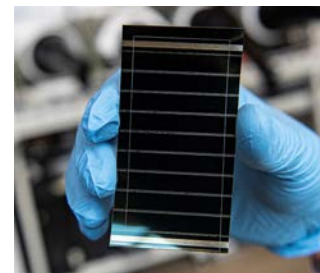
- ▶ relatively cheap
- ▶ last long (25 years)
- ▶ 70,600 MW installed
- ▶ ~50 nuclear power plants



Lason *Dreamstime.com*

Perovskites

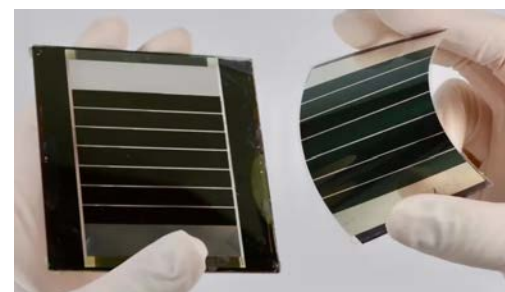
- ▶ relatively cheap
- ▶ new, still unstable
- ▶ but in the lab more efficient



Dennis Schroeder

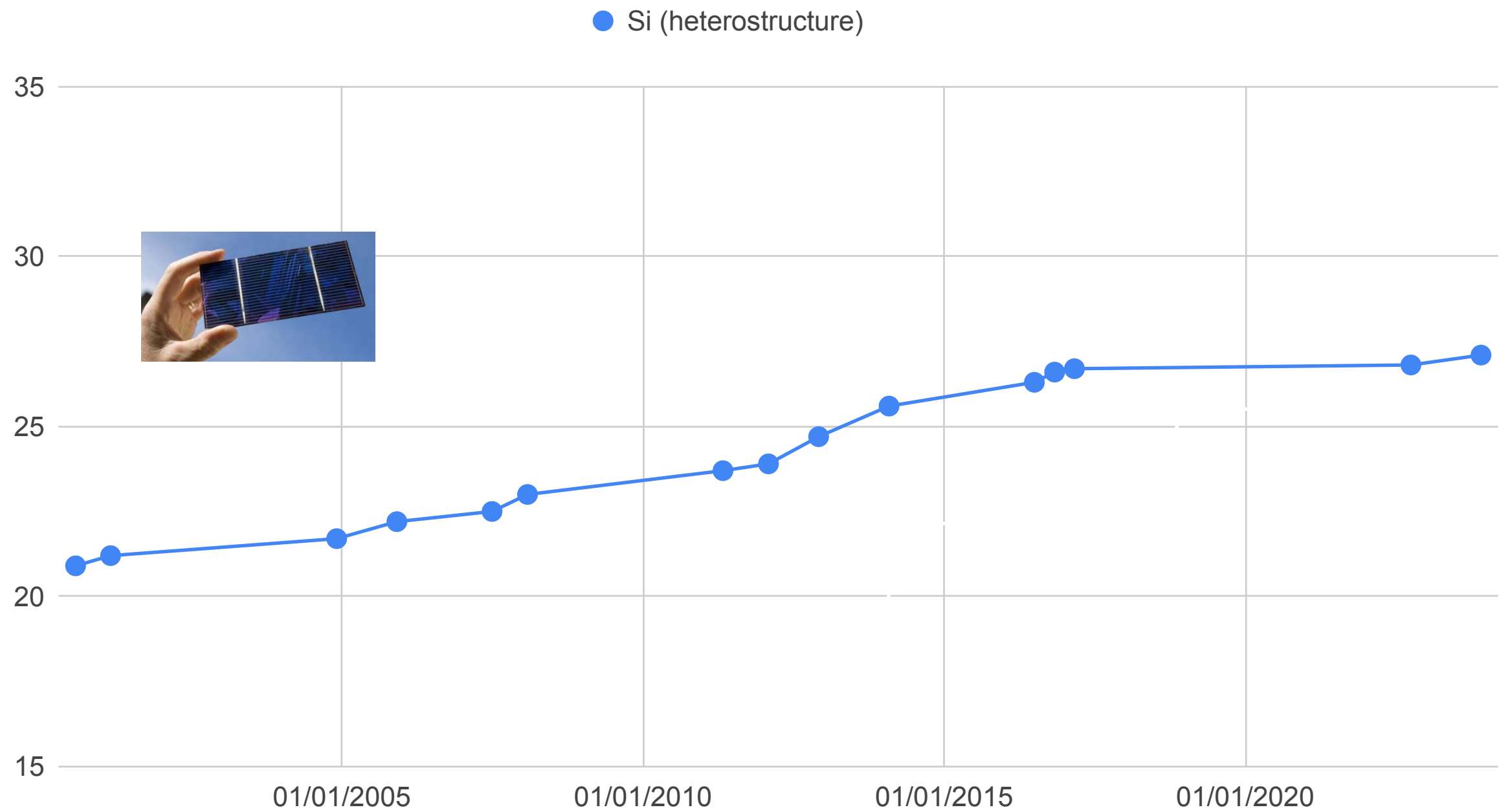


E. Kymakis

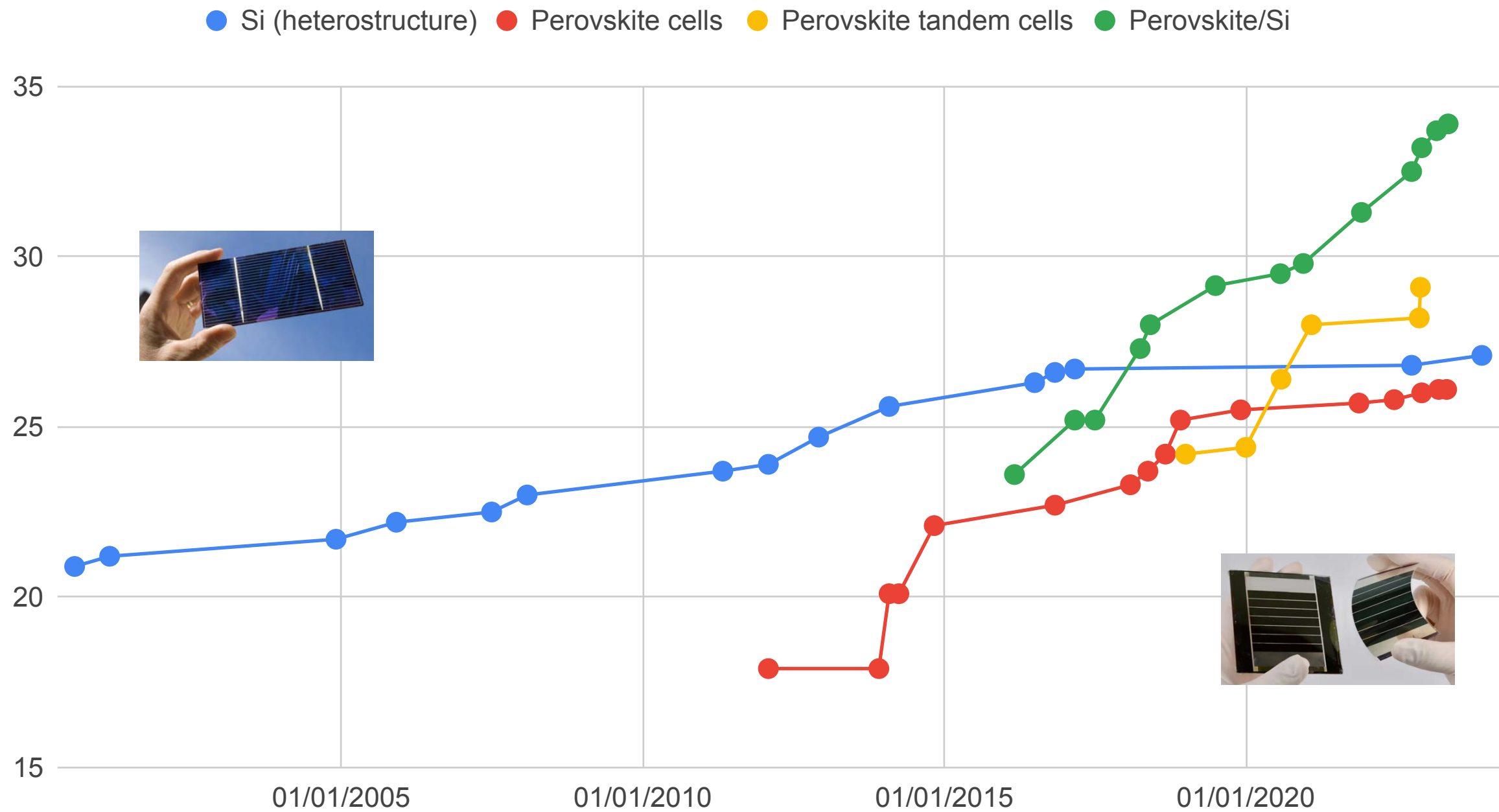


Kyoto University

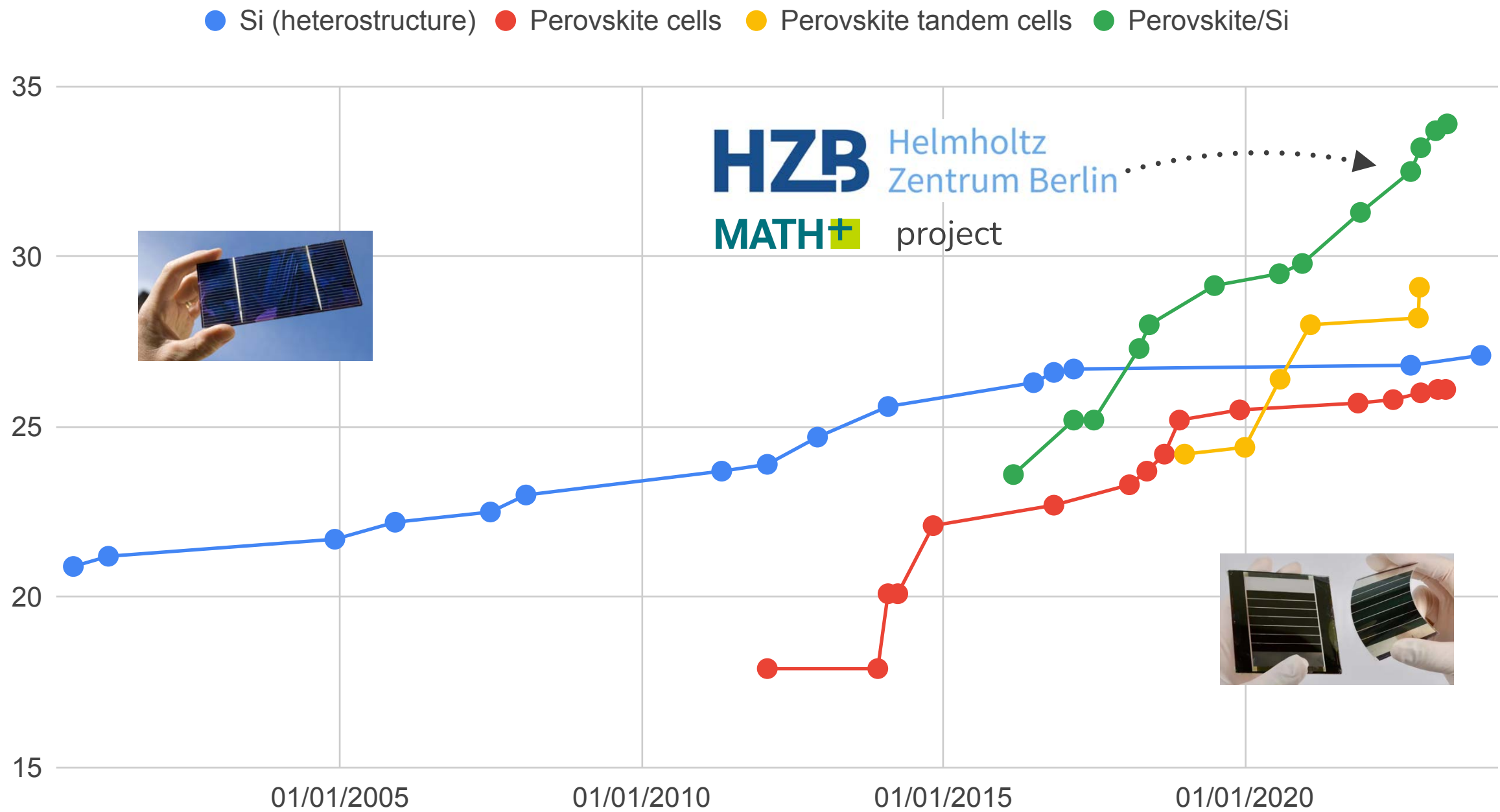
World-record efficiency [%]



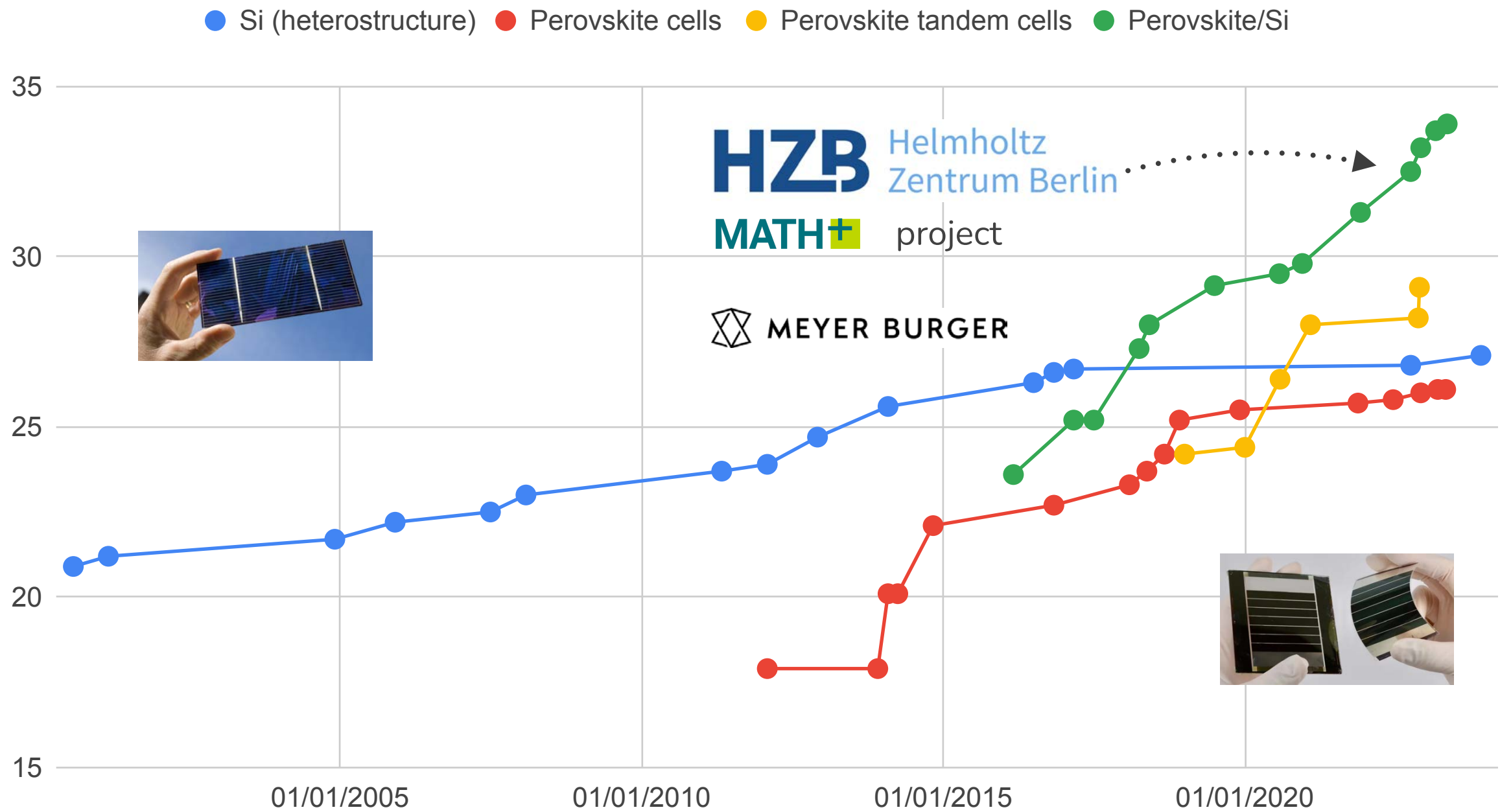
World-record efficiency [%]



World-record efficiency [%]



World-record efficiency [%]



Perovskites

Generic material structure

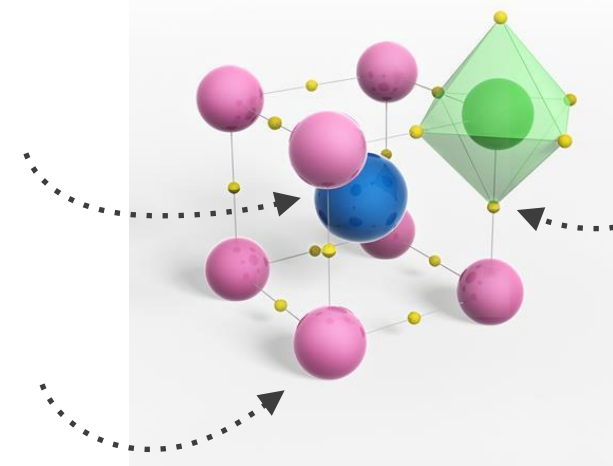


e.g. MAPI $(CH_3NH_3)^+Pb^{2+}(X^-)_3$

Cation *A*

Cation *B*

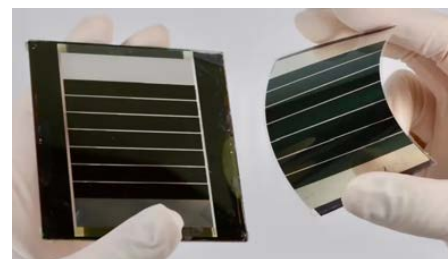
Anion *X*



Russian mineralogist Perovski

Applications

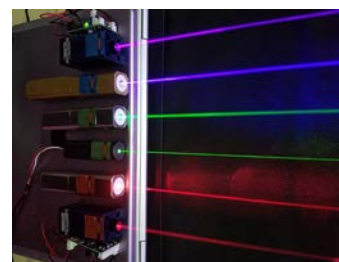
- ▶ solar cells
- ▶ photobatteries
- ▶ magnets
- ▶ lasers
- ▶ data storage



Dennis Schroeder



computer generated



彭嘉傑 - CC BY 2.5



Thor Balkhed



Jumia

How to turn this problem into mathematics?

Modeling ¹⁾



- ▶ charge transport
- ▶ drift-diffusion PDE

Analysis ^{2), 3)}

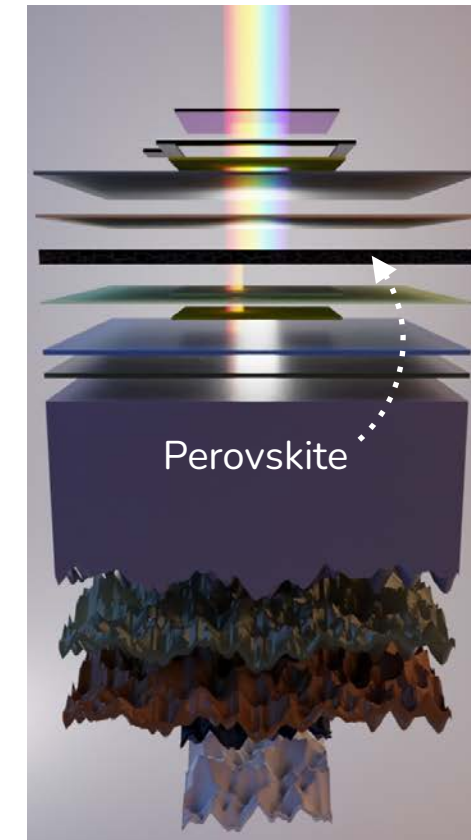


- ▶ existence of sol. for PDE
- ▶ two-point flux FVM
- ▶ existence of sol. for FVM

Simulation ^{2), 4)}



- ▶ different flux models

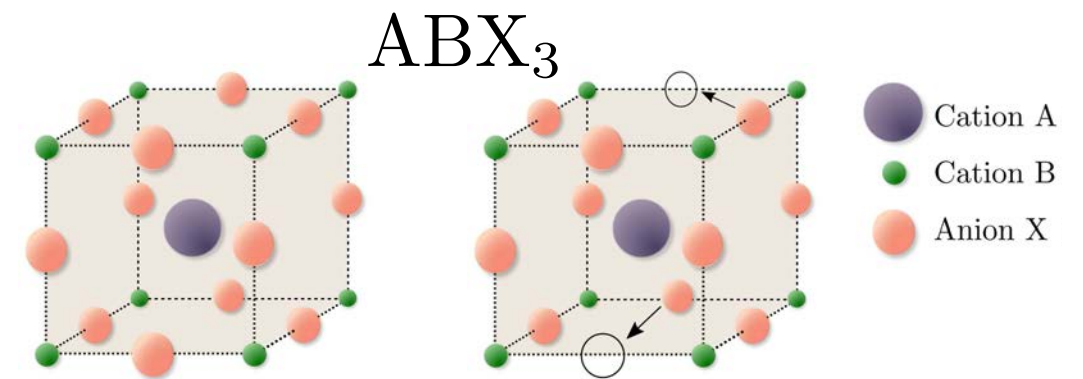


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- 1) D. Abdel, P. Vagner, J. Fuhrmann, P. Farrell. *Modelling charge transport in perovskite solar cells: Potential-based and limiting ion depletion*. *Electrochimica Acta*, 390: 138696, 2021.
 - 2) D. Abdel, C. Chainais-Hillairet, P. Farrell, M. Herda. *Numerical analysis of a finite volume scheme for charge transport in perovskite solar cells*. *IMA Journal of Numerical Analysis*, 2023
 - 3) D. Abdel, A Glitzky, M. Liero. *Analysis of a drift-diffusion model for perovskite solar cells*. Accepted for publication in *DCDS-B*, 2024.
 - 4) D. Abdel, N. Courtier, P. Farrell. *Volume exclusion effects in perovskite charge transport modeling*. *Optical and Quantum Electronics*, 55(884), 2023.

Modeling perovskite solar cells

Ion movement

- ▶ due to Schottky defects ions migrate
- ▶ ions move 10/15 orders more slowly

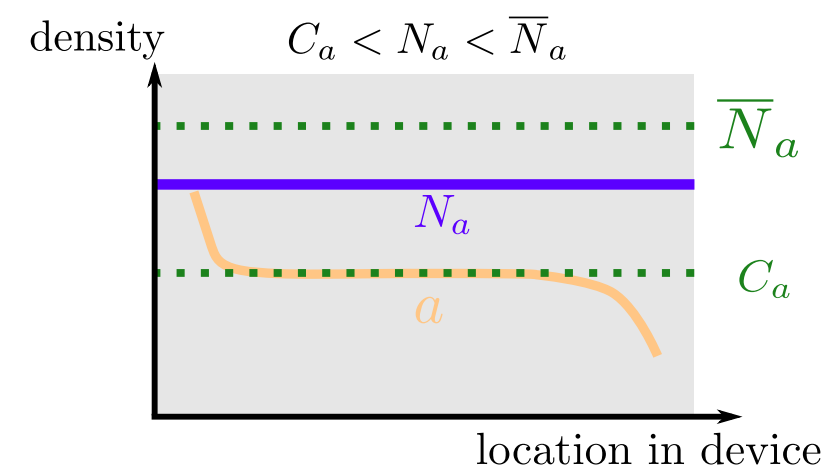


Potentials vs densities

- ▶ electrostatic/qF potentials of same order
- ▶ densities may jump at hetero interfaces
- ▶ gradient structure

Volume exclusion

- ▶ ions significantly bigger than electrons/holes
- ▶ ions cannot deplete without destroying the crystal



Drift-diffusion model

Transport layers

$$-\nabla \cdot (\varepsilon_s \nabla \psi) = q (C + p - n) \quad \text{Poisson}$$

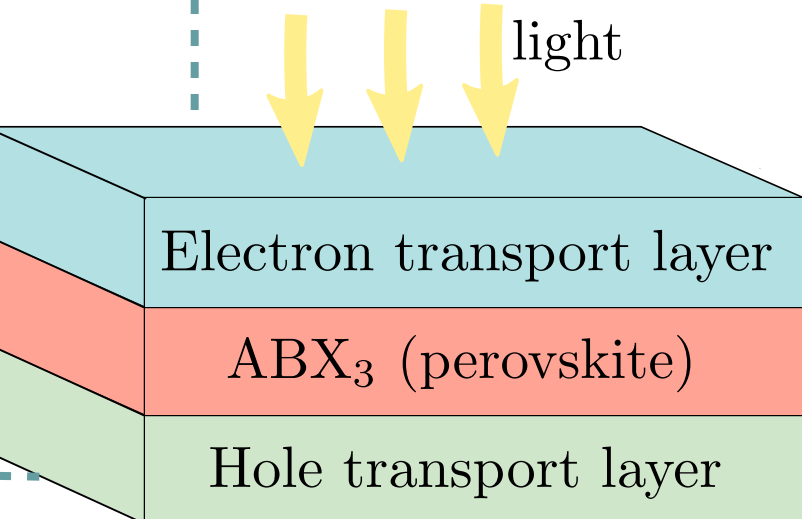
$$\begin{aligned} q\partial_t n - \nabla \cdot \mathbf{j}_n &= q(G - R), \\ q\partial_t p + \nabla \cdot \mathbf{j}_p &= q(G - R), \end{aligned} \quad \text{Cont. equations}$$

+ Dirichlet bc & ic

Perovskite layer

$$-\nabla \cdot (\varepsilon_s \nabla \psi) = q (C + p - n + a) \quad \text{Poisson}$$

$$\begin{aligned} q\partial_t n - \nabla \cdot \mathbf{j}_n &= q(G - R), \\ q\partial_t p + \nabla \cdot \mathbf{j}_p &= q(G - R), \\ q\partial_t a + \nabla \cdot \mathbf{j}_a &= 0 \end{aligned} \quad \text{Cont. equations}$$



+ hom. Neumann bc & ic

Drift-diffusion model

Transport layers

$$-\nabla \cdot (\varepsilon_s \nabla \psi) = q (C + p - n) \quad \text{Poisson}$$

$$q \partial_t n - \nabla \cdot \mathbf{j}_n = q(G - R), \quad \text{Cont. equations}$$

$$q \partial_t p + \nabla \cdot \mathbf{j}_p = q(G - R),$$

Current densities

$$\begin{aligned} \mathbf{j}_\alpha &= -z_\alpha^2 \mu_\alpha \alpha \nabla \varphi_\alpha \\ &= -z_\alpha q (D_\alpha \nabla \alpha + z_\alpha \mu_\alpha \alpha \nabla \psi) \end{aligned}$$

State equations

$$\alpha = N_\alpha \mathcal{F}_\alpha(\eta_\alpha), \quad \eta_\alpha = \left(z_\alpha \frac{\psi - \varphi_\alpha - E_\alpha / q}{U_T} \right)$$

Perovskite layer

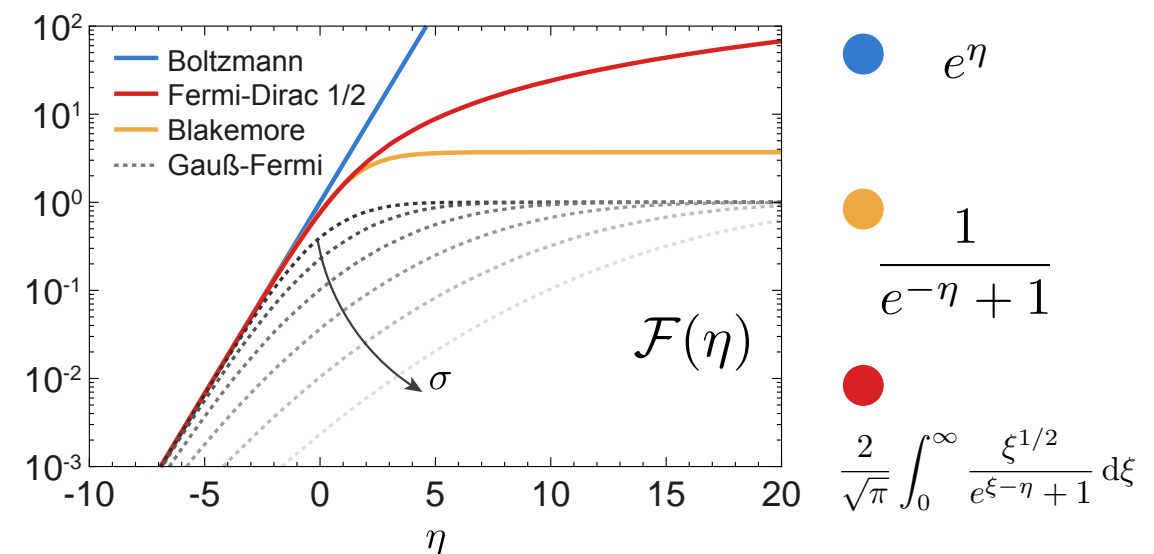
$$-\nabla \cdot (\varepsilon_s \nabla \psi) = q (C + p - n + a) \quad \text{Poisson}$$

$$q \partial_t n - \nabla \cdot \mathbf{j}_n = q(G - R), \quad \text{Cont. equations}$$

$$q \partial_t p + \nabla \cdot \mathbf{j}_p = q(G - R),$$

$$q \partial_t a + \nabla \cdot \mathbf{j}_a = 0$$

Statistics

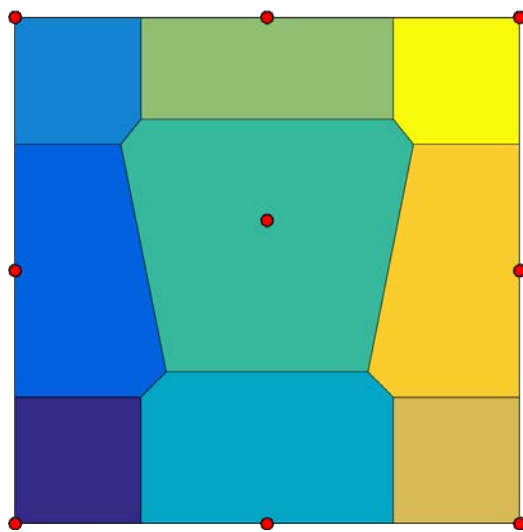


Finite volume discretization

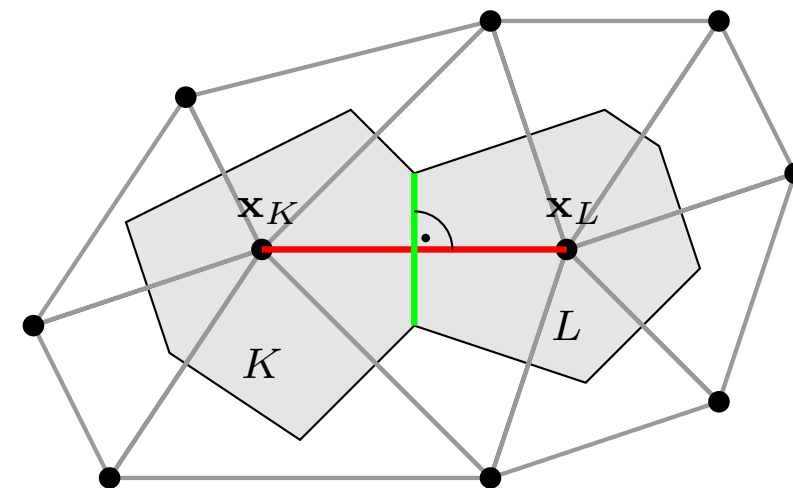
$$\nabla \cdot (\varepsilon \nabla \psi) + q(C + p - n) = 0$$

$$\frac{\partial}{\partial t} n - \frac{1}{q} \nabla \cdot \mathbf{j}_n - (G - R(n, p)) = 0$$

$$\frac{\partial}{\partial t} p + \frac{1}{q} \nabla \cdot \mathbf{j}_p - (G - R(n, p)) = 0$$



Voronoi tessellation



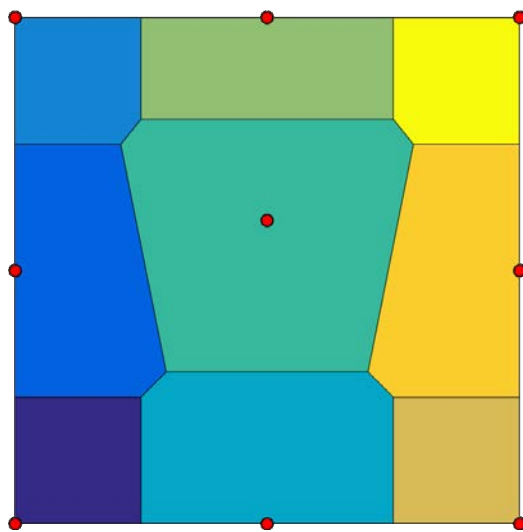
Flux along 1D edge

Finite volume discretization

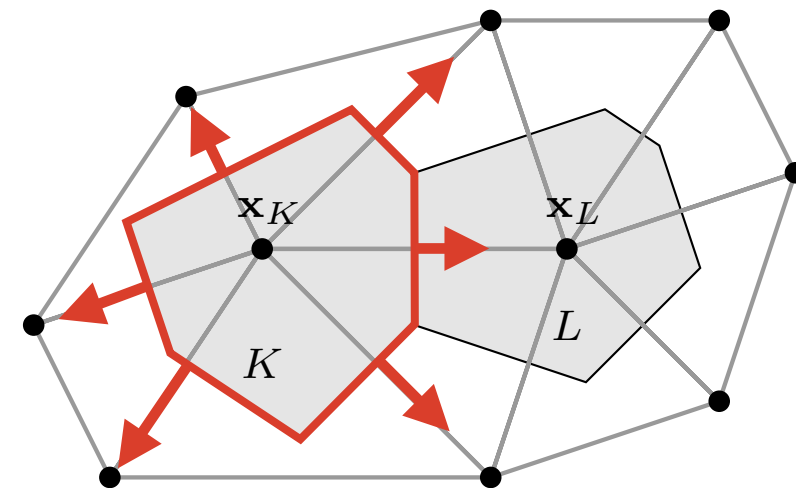
$$\sum_{L \in N(K)} \sigma_{KL} (\mathbf{x}_L - \mathbf{x}_K) \cdot (\varepsilon(\psi_L - \psi_K)/h_{K,L}) + q |K| (C_K + p_K - n_K) = 0$$

$$\frac{\partial}{\partial t} |K| n_K - \frac{1}{q} \sum_{L \in N(K)} |\sigma_{KL}| j_{n,KL} - |K| (G_K - R(n_K, p_K)) = 0$$

$$\frac{\partial}{\partial t} |K| p_K + \frac{1}{q} \sum_{L \in N(K)} |\sigma_{KL}| j_{p,KL} - |K| (G_K - R(n_K, p_K)) = 0$$



Voronoi tessellation



Flux along 1D edge

Existence of solutions

Continuous PDE model

- ▶ **Regularized** state equations and reaction terms
- ▶ Solvability shown by using discrete arguments and passing to the continuous limit
- ▶ **Moser iteration** technique leads to a priori estimates for densities and potentials, independent of the regularisation level
- ▶ Existence of the original problem

Discrete FVM model

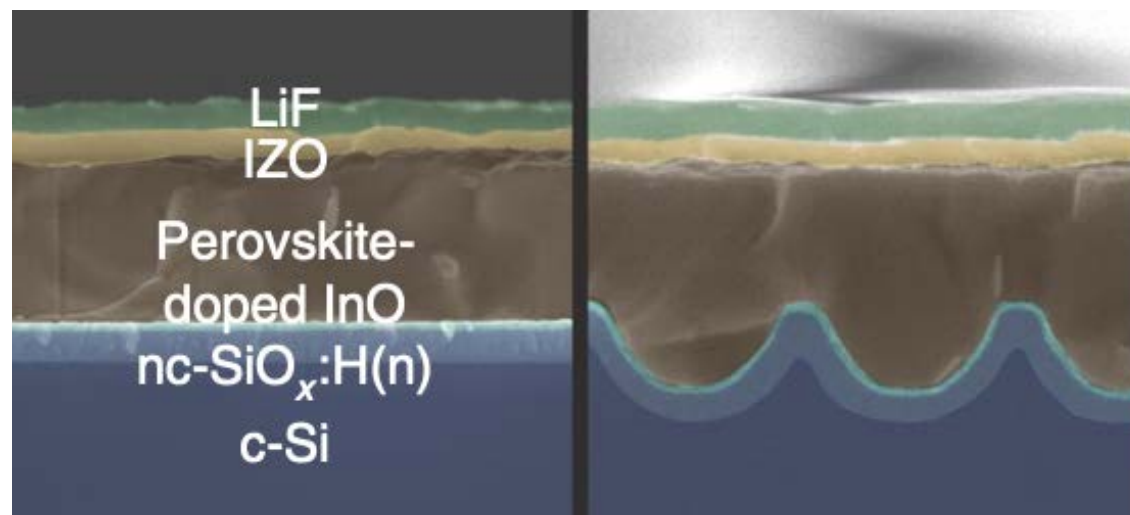
- ▶ SEDAN flux approximation (**Scharfetter-Gummel** type)
- ▶ Numerical **entropy-dissipation** relation
- ▶ Ensures a priori estimates for the densities and potentials
- ▶ Existence of numerical solution via **Brouwer's fixed point theorem**
- ▶ Open-source software tool: ChargeTransport.jl

D. Abdel, C. Chainais-Hillairet, P. Farrell, M. Herda. *Numerical analysis of a finite volume scheme for charge transport in perovskite solar cells*. IMA Journal of Numerical Analysis, 2023

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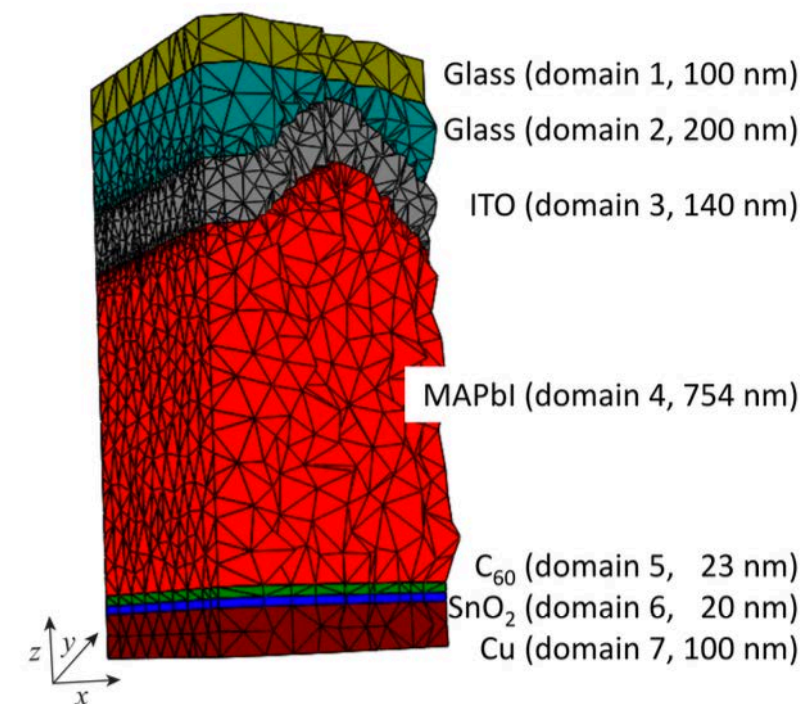
Simulation

- ▶ 3D nanotextured perovskite solar cell
- ▶ current project with Helmholtz Zentrum and Zuse Institute
- ▶ solution converges quadratically in space, linear in time
- ▶ relative entropy decays exponentially (as predicted by theory)



planar interface

nanotextured



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Thank you for your attention!



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